

July 21, 1964

Dr. John Dismukes  
Radio Corporation of America  
RCA Laboratories  
David Sarnoff Research Center  
Princeton, New Jersey

Dear Dr. Dismukes:

Thank you very much for your letter of July 17 and for the samples of germanium and silicon powders and also the samples of phosphorus doped germanium - silicon material. We very much appreciate your generosity in making these materials available to us. We will certainly inform you of results as our research with these systems progresses.

Very truly yours,

H. Tracy Hall  
Director of Research  
Room 224 ELB

HTH/lw



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RADIO CORPORATION OF AMERICA  
RCA LABORATORIES  
*David Sarnoff Research Center*  
PRINCETON, N. J.



July 17, 1964

Prof. H. Tracy Hall  
Director of Research  
Room 224 ELB  
Research Division  
Brigham Young University  
Provo, Utah

Dear Prof. Hall,

Enclosed are some samples of Ge and Si, both powders and slices from the batch we used for our studies.

Also included are samples of phosphorus doped 28at%Ge, slices 5,6,8,9 of ingot #100. The thermoelectric power of the material is about  $-530\mu\text{V}/^\circ\text{C}$  at  $300^\circ\text{K}$ , carrier concentration about  $1 \times 10^{18} \text{ cm}^{-3}$ .

I will cut more phosphorus doped samples from other compositions and send them later.

Sincerely,

*John Dismukes*  
John Dismukes

JD:ez

Enclosure